

WHAT IS CLAIMED IS:

1. A method for fabricating N-type doped polycrystalline silicon, comprising:
providing a wafer;
placing the wafer in a reaction chamber;
5 introducing a reaction gas source, an N-type doped gas source and a gas source of a catalyst into the reaction chamber; and
performing a chemical vapor deposition process to form an N-type doped polycrystalline silicon film.

10 2. The method of claim 1, wherein the reaction gas source is selected from a group consisting of SiH_2Cl_2 , SiHCl_3 and SiCl_4 .

3. The method of claim 2, wherein the catalyst includes B_2H_6 .

15 4. The method of claim 1, wherein the reaction gas includes SiCl_4 .

5. The method of claim 2, wherein the catalyst includes B_2H_6 .

6. The method of claim 1, wherein the catalyst includes B_2H_6 .

20 7. The method of claim 1, wherein the doped gas source includes PH_3 .

8. A method for fabricating N-type doped polycrystalline silicon, comprising:
providing a wafer;

placing the wafer in a reaction chamber;

introducing silane containing chlorine, PH_3 and B_2H_6 as gas source into the reaction chamber for increasing deposition rate, wherein an amount of B_2H_6 is lower than that of the PH_3 ; and

5 performing a chemical vapor deposition process to form a N-type doped polycrystalline silicon film.

9. The method of Claim 8, wherein the silane containing chlorine is selected from a group consisting of SiH_2Cl_2 , SiHCl_3 and SiCl_4 .

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10. A method for fabricating N-type doped polycrystalline silicon, comprising:

providing a wafer;

placing the wafer in a reaction chamber;

introducing silane containing chlorine and a catalyst as a gas source into the reaction chamber to increase rate of deposition;

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performing a chemical vapor deposition process to form a polycrystalline film; and

performing an N-type dopant implantation process to form an N-type doped polycrystalline silicon film.

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11. The method of claim 10, wherein the silane containing chlorine is selected from a group consisting of SiH_2Cl_2 , SiHCl_3 and SiCl_4 .

12. The method of claim 10, wherein the catalyst includes B_2H_6 .

Year	Country	Population (millions)	Urban population (millions)	Urban population (%)	Population growth rate (%)	Urban population growth rate (%)
1950	India	366	100	27.3	1.8	1.8
1955	India	390	110	28.2	2.0	2.0
1960	India	414	120	29.0	2.2	2.2
1965	India	438	130	29.7	2.4	2.4
1970	India	462	140	30.3	2.6	2.6
1975	India	486	150	30.9	2.8	2.8
1980	India	510	160	31.4	3.0	3.0
1985	India	534	170	31.8	3.2	3.2
1990	India	558	180	32.3	3.4	3.4
1995	India	582	190	32.8	3.6	3.6
2000	India	606	200	33.2	3.8	3.8
2005	India	630	210	33.3	4.0	4.0
2010	India	654	220	33.6	4.2	4.2
2015	India	678	230	33.9	4.4	4.4
2020	India	702	240	34.2	4.6	4.6
2025	India	726	250	34.4	4.8	4.8
2030	India	750	260	34.7	5.0	5.0
2035	India	774	270	35.0	5.2	5.2
2040	India	798	280	35.2	5.4	5.4
2045	India	822	290	35.4	5.6	5.6
2050	India	846	300	35.5	5.8	5.8
2055	India	870	310	35.7	6.0	6.0
2060	India	894	320	35.9	6.2	6.2
2065	India	918	330	36.0	6.4	6.4
2070	India	942	340	36.2	6.6	6.6
2075	India	966	350	36.3	6.8	6.8
2080	India	990	360	36.4	7.0	7.0
2085	India	1014	370	36.5	7.2	7.2
2090	India	1038	380	36.6	7.4	7.4
2100	India	1062	390	36.7	7.6	7.6

14. The method of claim 10, wherein the dopant of the N-type dopant implantation
5 process includes phosphorous ions